ERRATUM

Characterisation of Ar Ion Laser Induced CVD Silicon Films: Deposition, Crystallographic Texture and Phosphorous Doping

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- 1) On page 214, read $\tilde{v}$ for v in Eqs. (6) and (7) and discussion following Eq. (7) to obtain Eq. (8).
- 2) On page 214, Column 2, line 11, read $\ln d \propto -1/I$ for $\ln d \propto 1/I$.
- 3) On page 216, in Eq. (11), read J_{th} for V_{th} .
- 4) On page 215, Table II: Conductivity Data for

Various Pressures, contains a few errors and the corrected table is:

Table II. Conductivity Data for Various Pressures

PH ₃ partial pressure (in Torr)	N_D and σ expected for C-Si at 300 K		σ ($K\Omega$ cm) ⁻¹ observed for LCVD film at 300 K	E_{act} (eV)
	N_D (10 ¹⁶ cm ⁻³)	σ (Ω cm) ⁻¹		
0	—	—	3.87×10^{-3}	0.48
0.04	0.6	1.1	0.24	0.32
0.12	1.8	2.8	0.77	0.28
0.20	3.0	4.4	1.38	0.23
0.30	4.5	5.9	3.67	0.20